

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

2SA1013

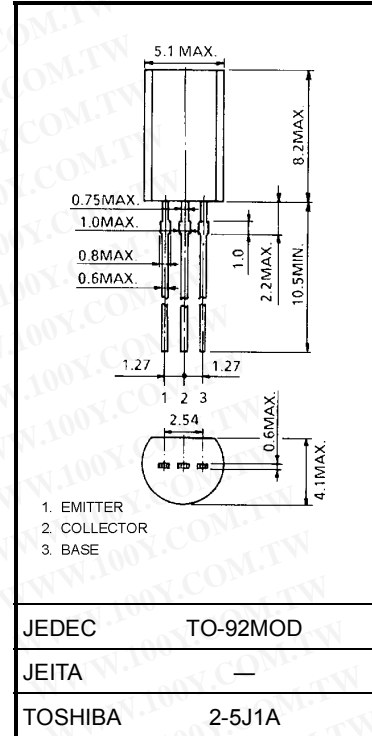
Color TV Vertical Deflection Output Applications
Power Switching Applications

Unit: mm

- High voltage: $V_{CEO} = -160$ V
- Large continuous collector current capability
- Recommended for vertical deflection output & sound output applications for line-operated TV.
- Complementary to 2SC2383.

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-160	V
Collector-emitter voltage	V_{CEO}	-160	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-1	A
Base current	I_B	-0.5	A
Collector power dissipation	P_C	900	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 150	$^\circ\text{C}$



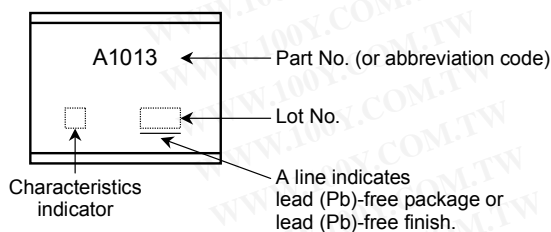
Weight: 0.36 g (typ.)

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

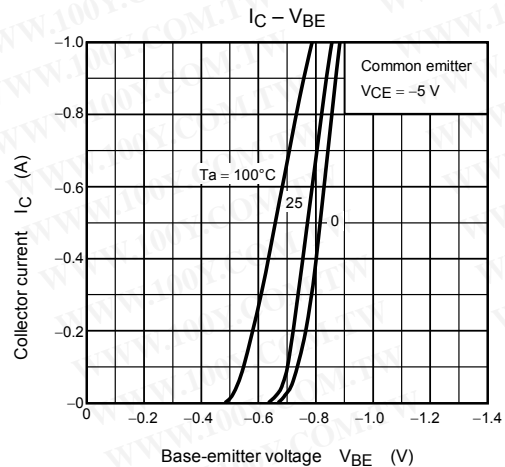
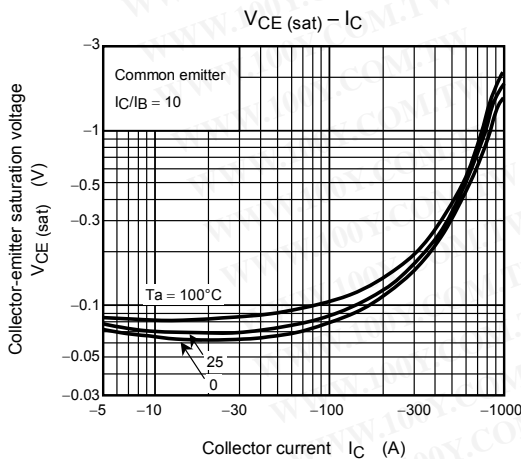
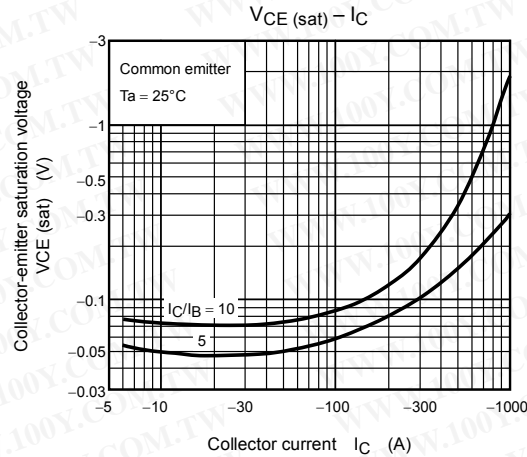
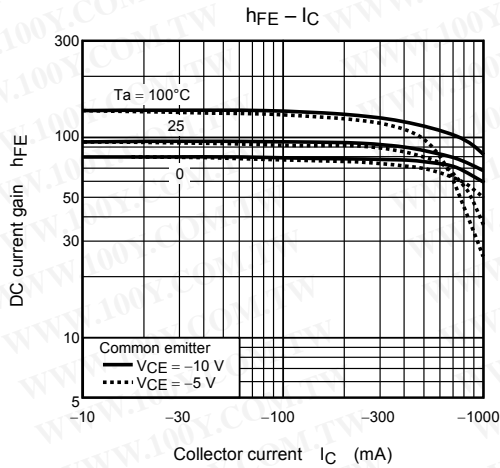
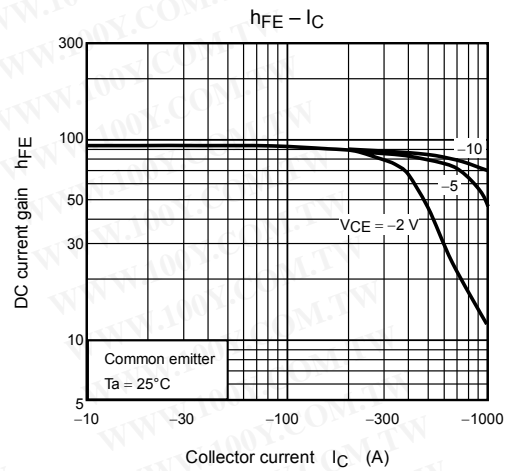
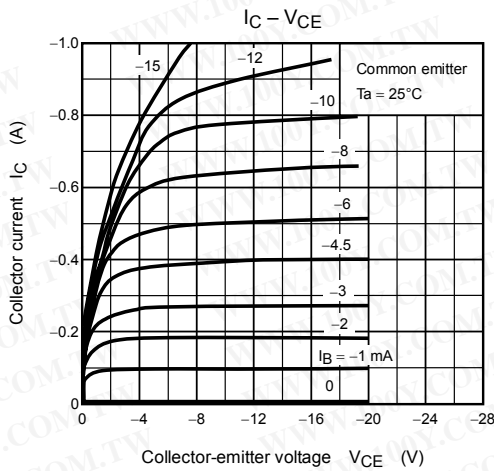
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -150$ V, $I_E = 0$	—	—	-1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6$ V, $I_C = 0$	—	—	-1.0	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10$ mA, $I_B = 0$	-160	—	—	V
DC current gain	h_{FE} (Note)	$V_{CE} = -5$ V, $I_C = -200$ mA	60	—	200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500$ mA, $I_B = -50$ mA	—	—	-1.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = -5$ V, $I_C = -5$ mA	-0.45	—	-0.75	V
Transition frequency	f_T	$V_{CE} = -5$ V, $I_C = -200$ mA	15	50	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10$ V, $I_E = 0$, $f = 1$ MHz	—	—	35	pF

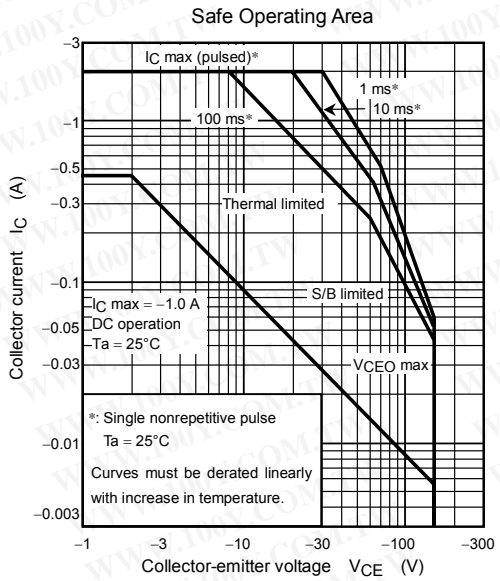
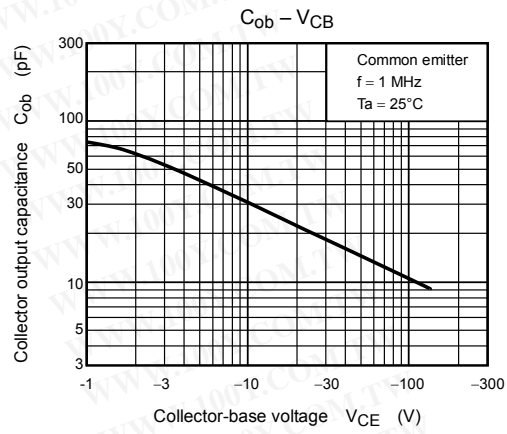
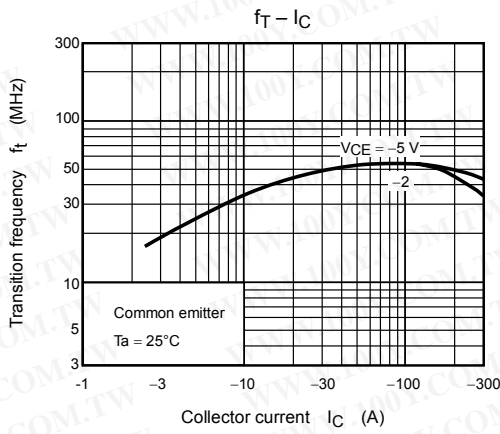
Note: h_{FE} classification R: 60 to 120, O: 100 to 200

Marking



勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
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